



Si4947ADY vs. Si4947DY

Description: Dual P-Channel, 30 V (D-S) MOSFET
Package: SO-8
Pin Out: Identical

Part Number Replacements

Si4947ADY-T1-E3 Replaces Si4947DY-E3

Si4947ADY-T1 Replaces Si4947DY-T1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)					
Parameter	Symbol	Si4947ADY	Si4947DY	Unit	
Drain-Source Voltage	V_{DS}	- 30	- 30	V	
Gate-Source Voltage	V_{GS}	± 20	± 20		
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	- 3.9	- 3.5	A
	$T_A = 70\text{ }^\circ\text{C}$		- 3.1	- 2.8	
Pulsed Drain Current	I_{DM}	- 20	- 20		
Continuous Source Current (MOSFET Diode Conduction)	I_S	- 1.7	- 1.7		
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	2.0	2.0	W
	$T_A = 70\text{ }^\circ\text{C}$		1.3	1.3	
Operating Junction and Storage Temperature Range	T_J and T_{stg}	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	R_{thJA}	62.5	62.5	$^\circ\text{C/W}$	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)								
Parameter	Symbol	Si4947ADY			Si4947DY			Unit
		Min	Typ	Max	Min	Typ	Max	
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	- 1.0			- 1.0			V
Gate-Body Leakage	I_{GSS}			± 100			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}			- 1			- 1	μA
On-State Drain Current	$V_{GS} = - 10\text{ V}$ $I_{D(on)}$	- 15			- 15			A
Drain-Source On-Resistance	$V_{GS} = - 10\text{ V}$ $r_{DS(on)}$		0.062	0.080		0.066	0.085	Ω
	$V_{GS} = - 4.5\text{ V}$		0.105	0.135		0.125	0.19	
Forward Transconductance	g_{fs}		5.0			5.0		S
Diode Forward Voltage	V_{SD}		- 0.82	- 1.2		- 0.8	- 1.2	V
Dynamic								
Total Charge	Q_g^1		5.8	8		8.7	15	nC
Gate-Source Charge	Q_{gs}		2			1.9		
Gate-Drain Charge	Q_{gd}		1.9			1.3		
Switching								
Turn-On Time	$t_{d(on)}$		8	15		7	15	ns
	t_r		9	18		9	18	
Turn-Off Time	$t_{d(off)}$		21	40		14	27	
	t_f		10	20		8	15	
Source-Drain Reverse Recovery Time	t_{rr}		27	40		50	80	

1. For Si4947ADY, $V_{GS} = 5\text{ V}$. For Si4947DY, $V_{GS} = 10\text{ V}$.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.